

Geoffrey Avit

List of Publications by Year in descending order

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Version: 2024-02-01

11
papers

237
citations

1306789

7
h-index

1281420

11
g-index

11
all docs

11
docs citations

11
times ranked

293
citing authors

| # | ARTICLE | IF | CITATIONS |
|----|--|-----|-----------|
| 1 | Formation of voids in selective area growth of InN nanorods in SiN _x on GaN templates. Nano Futures, 2020, 4, 025002. | 1.0 | 5 |
| 2 | Morphological Control of InN Nanorods by Selective Area Growth—Hydride Vapor-Phase Epitaxy. Crystal Growth and Design, 2020, 20, 2232-2239. | 1.4 | 5 |
| 3 | Selective growth of ordered hexagonal InN nanorods. CrystEngComm, 2019, 21, 2702-2708. | 1.3 | 13 |
| 4 | Compositional control of homogeneous InGaN nanowires with the In content up to 90%. Nanotechnology, 2019, 30, 044001. | 1.3 | 12 |
| 5 | Circumventing the miscibility gap in InGaN nanowires emitting from blue to red. Nanotechnology, 2018, 29, 465602. | 1.3 | 22 |
| 6 | Crystal engineering by tuning the growth kinetics of GaN 3-D microstructures in SAG-HVPE. CrystEngComm, 2018, 20, 6207-6213. | 1.3 | 6 |
| 7 | Influence of Silicon on the Nucleation Rate of GaAs Nanowires on Silicon Substrates. Journal of Physical Chemistry C, 2018, 122, 19230-19235. | 1.5 | 15 |
| 8 | GaN Rods Grown on Si by SAG-HVPE toward GaN HVPE/InGaN MOVPE Core/Shell Structures. Crystal Growth and Design, 2016, 16, 2509-2513. | 1.4 | 8 |
| 9 | Vapor liquid solid-hydride vapor phase epitaxy (VLS-HVPE) growth of ultra-long defect-free GaAs nanowires: Ab initio simulations supporting center nucleation. Journal of Chemical Physics, 2014, 140, 194706. | 1.2 | 11 |
| 10 | Ultralong and Defect-Free GaN Nanowires Grown by the HVPE Process. Nano Letters, 2014, 14, 559-562. | 4.5 | 58 |
| 11 | Record Pure Zincblende Phase in GaAs Nanowires down to 5 nm in Radius. Nano Letters, 2014, 14, 3938-3944. | 4.5 | 82 |